

Description

Product Summary

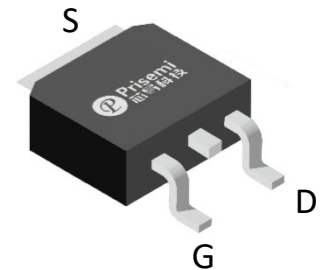
$V_{DS}(V)$	$R_{DS(on)}(m\Omega)(Typ)$	$I_D(A)$
700	125	18

Feature

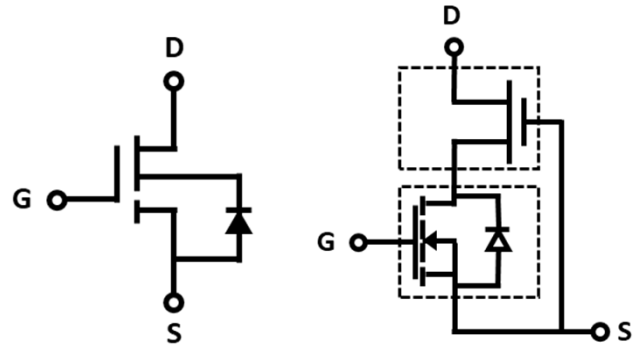
- Easy to use, compatible with standard gate drivers
- Excellent $Q_G \times R_{DS(on)}$ figure of merit (FOM)
- Low Q_{RR} , no free-wheeling diode required
- Low switching loss
- RoHS compliant and Halogen-free

Applications

- High efficiency power supplies
- Telecom and datacom
- Automotive
- Servo motors



TO-252 (Top View)



Schematic Symbol

Cascode Device Structure

Absolute maximum rating@25°C

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DS}	700	V
Gate-Source Voltage		V_{GS}	± 20	V
Transient Drain-Source Voltage ¹⁾		V_{TDS}	800	V
Continuous Drain Current	$T_C=25^\circ C$	I_D	18	A
	$T_C=100^\circ C$		12	
Pulsed Drain Current (Pulse Width: 100μs)	$T_C=25^\circ C$	I_{DM}	49	A
	$T_C=150^\circ C$		37	
Power Dissipation		P_D	74	W
Soldering Peak Temperature		T_{CSOLD}	260	°C
Operating Junction and Storage Temperature		T_J, T_{STG}	-55 to 150	°C

Thermal Resistance

Parameter	Symbol	Min	Typ	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	-	1.7	-	°C/W
Thermal Resistance, Junction-to-Ambient ²⁾	$R_{\theta JA}$	-	50	-	°C/W

Electrical characteristics per line@25°C (unless otherwise specified)

Parameter	Symbol	Conditions		Min.	Typ.	Max.	Units
Statistic Characteristics							
Maximum Drain-Source Voltage	V _{DS-Max}	V _{GS} = 0V		700	-	-	V
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} = 0V, I _D = 250μA		-	1000	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =700V, V _{GS} =0V	T _J =25°C	-	8	20	μA
			T _J =150°C	-	50	-	
Gate-Body Leakage Current	I _{GSS}	V _{GS} = ±20V, V _{DS} = 0V		-	-	±150	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 500μA		3	4	5	V
Gate threshold voltage temperature coefficient	ΔV _{GS(th)} /T _J			-	-10.7	-	mV/°C
Drain-Source On-State Resistance ³⁾	R _{DS(ON)}	V _{GS} =12V, I _D =4A	T _J =25°C	-	125	160	mΩ
			T _J =150°C	-	250	-	
Dynamic Characteristics							
Input Capacitance	C _{iss}	V _{DS} = 400V, V _{GS} = 0V, f = 1MHz		-	563	-	pF
Output Capacitance	C _{oss}			-	28	-	
Reverse Transfer Capacitance	C _{rss}			-	1.1	-	
Effective Output Capacitance, Energy Related	C _{o(er)}	V _{GS} = 0V, V _{DS} = 0-400V		-	43	-	pF
Effective Output Capacitance, Time Related	C _{o(tr)}			-	90	-	
Output Charge	Q _{oss}			-	36	-	nC
Turn-on Delay Time	t _{d(on)}	V _{DS} = 400V, I _D = 12A, V _{GS} =0-12V, R _G =47Ω		-	50	-	ns
Turn-on Rise Time	t _r			-	6	-	
Turn-Off Delay Time	t _{d(off)}			-	80	-	
Turn-Off Fall Time	t _f			-	5	-	
Total Gate Charge	Q _g	V _{DS} = 400V, I _D = 12A, V _{GS} =0-12V		-	16	-	nC
Gate-Source Charge	Q _{gs}			-	4.8	-	
Gate-Drain Charge	Q _{gd}			-	4.4	-	
Reverse Diode Characteristics							
Diode Forward Voltage	V _{SD}	V _{GS} =0V, I _S =6A		-	1.1	-	V
		V _{GS} =0V, I _S =12A	T _J =25°C	-	1.5	-	
			T _J =150°C	-	2	-	
Reverse Recovery Time	t _{rr}	V _{GS} =0V, I _S =12A, V _{DD} =400V, di/dt=1000A/μs		-	21	-	ns
Reverse Recovery Charge	Q _{rr}			-	36	-	μC

Notes:

- Off-state spike duty cycle < 0.01, spike duration < 2μs
- Device on one layer epoxy PCB for drain connection (vertical and without air stream cooling, with 6cm²copper area and 70μm thickness)
- Dynamic on-resistance; see Figure 19 and 20 for test circuit and configurations

Typical Characteristics

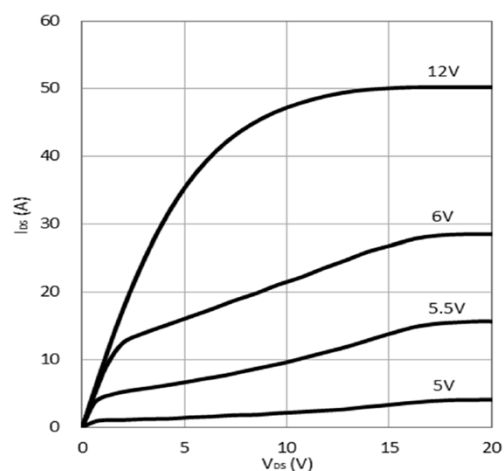
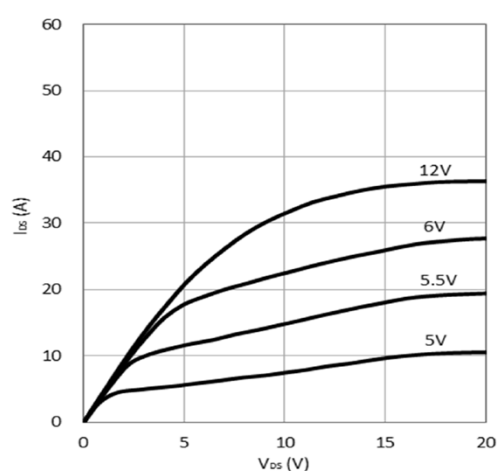
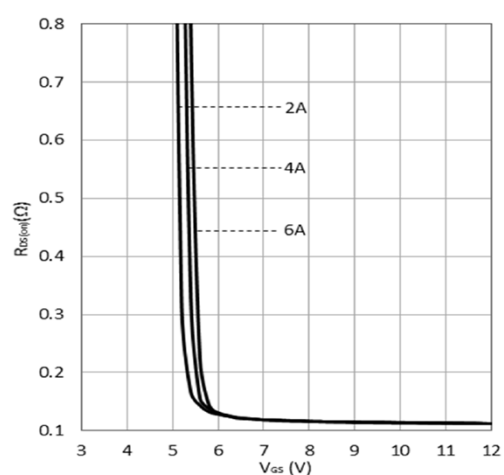
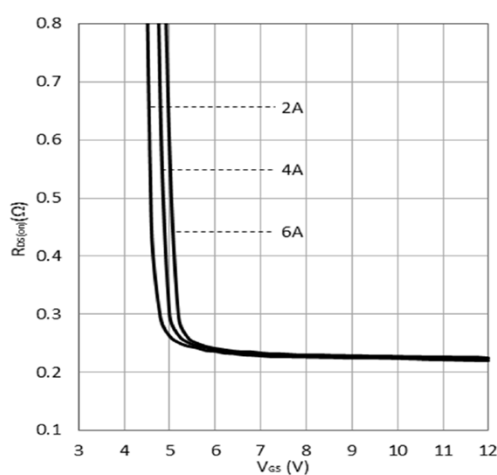
Figure 1. Typical Output Characteristics $T_J=25^\circ\text{C}$ Parameter: V_{DS} Figure 2. Typical Output Characteristics $T_J=150^\circ\text{C}$ Parameter: V_{DS} Figure 3. Typical Drain to Source On-resistance $T_J=25^\circ\text{C}$ Parameter: I_D Figure 4. Typical Drain to Source On-resistance $T_J=150^\circ\text{C}$ Parameter: I_D

Figure 5. Typical Transfer Characteristics

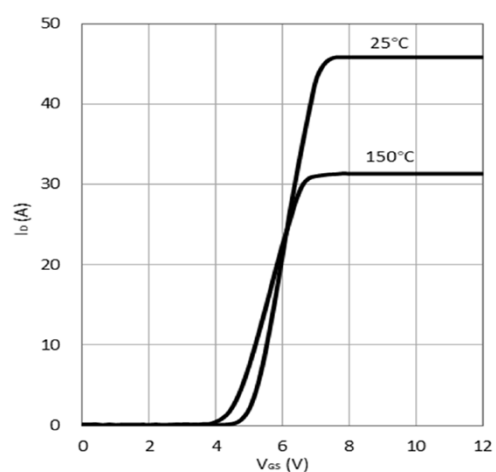
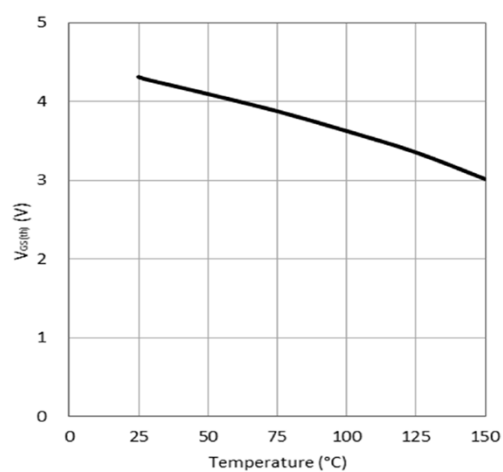
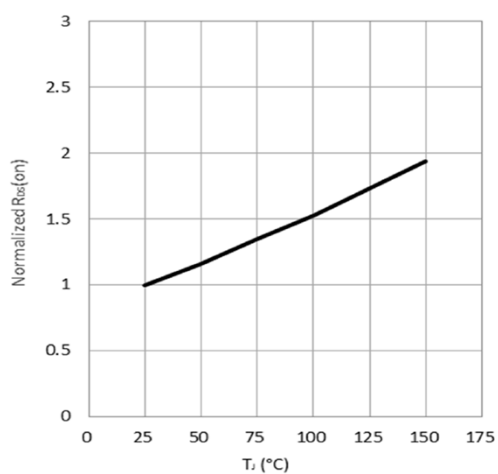
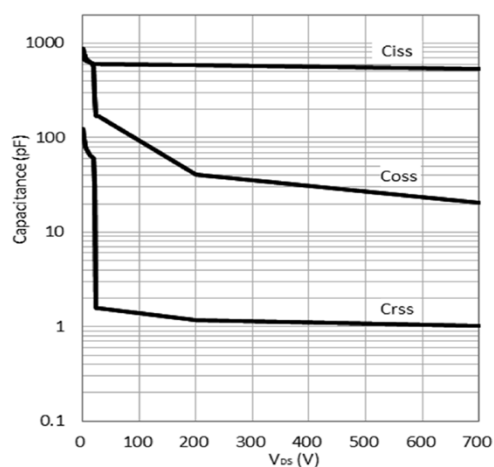
 $V_{DS}=10\text{V}$, Parameter: T_J Figure 6. $V_{GS(th)}$ Vs Temperature Characteristics $I_D=500\mu\text{A}$

Figure 7. Normalized On-resistance



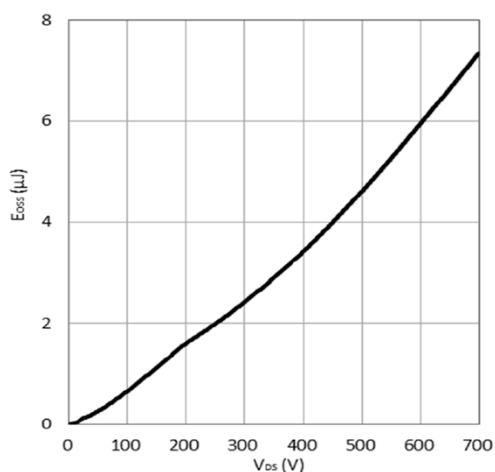
$I_D=4A$, $V_{GS}=12V$

Figure 8. Typical Capacitance



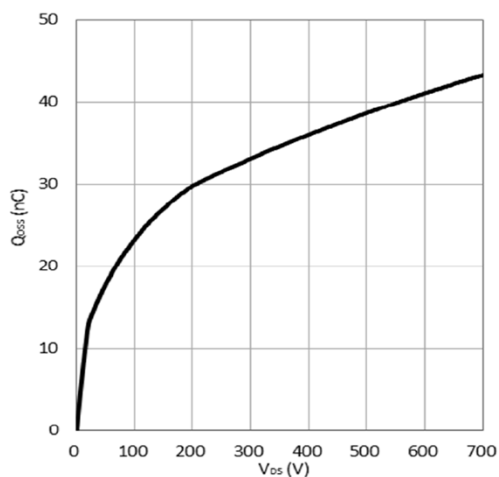
$V_{GS}=0V$, $f=1MHz$

Figure 9. Typical Coss Stored Energy



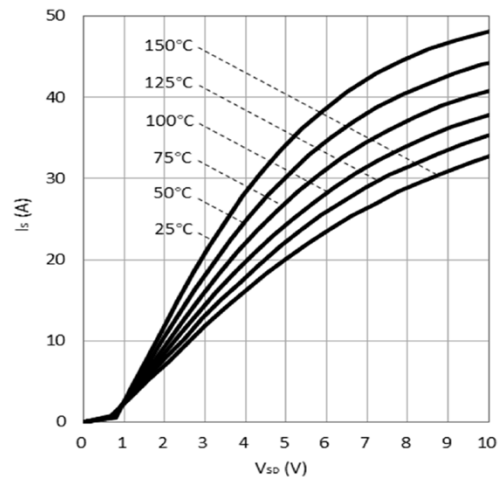
$V_{GS}=0V$, $f=1MHz$

Figure 10. Typical Qoss



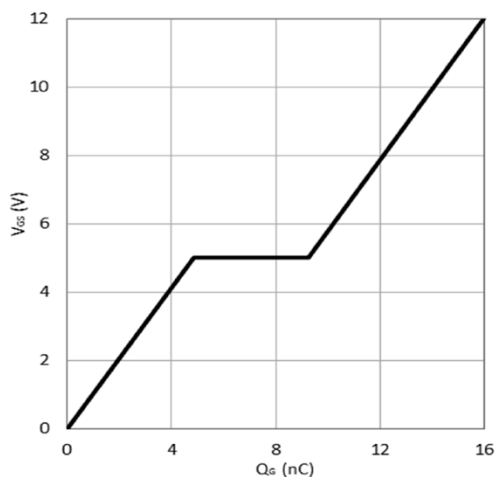
$V_{GS}=0V$, $f=1MHz$

Figure 11. Forward Characteristic of Rev. Diode



$I_s=f(V_{SD})$, Parameter T_j

Figure 12. Typical Gate Charge



$I_{DS}=12A$, $V_{DS}=400V$

Figure 13. Power Dissipation

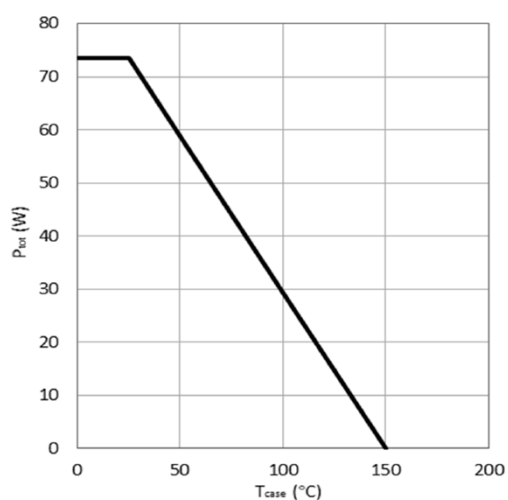


Figure 14. Current Derating

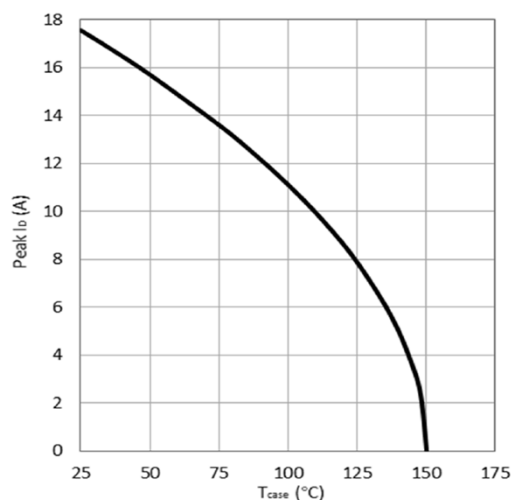


Figure 15. Transient Thermal Resistance

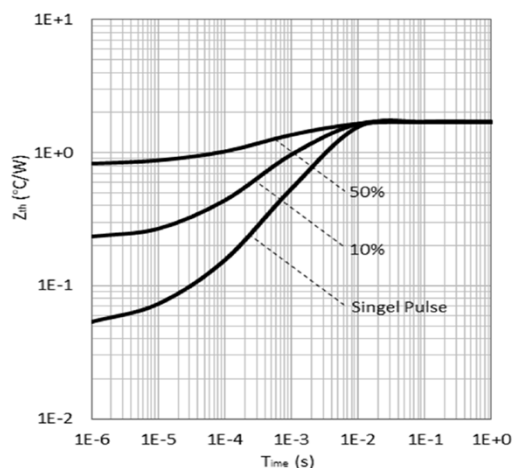
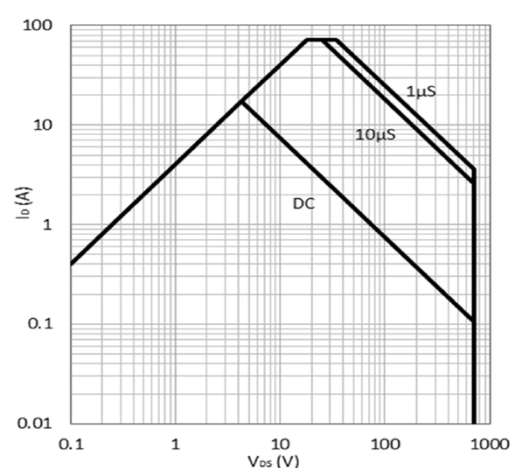
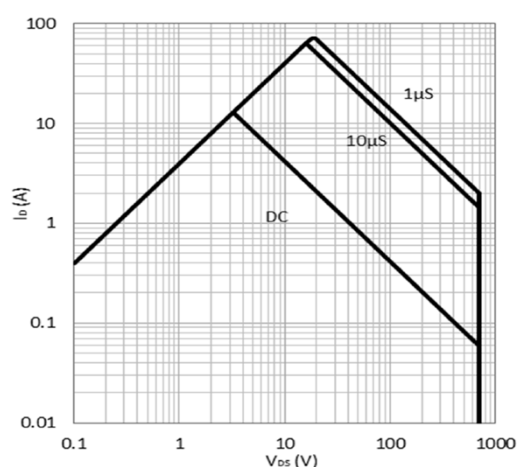


Figure 16. Safe Operating Area T_C=25°C



calculated based on thermal limit

Figure 17. Safe Operating Area T_C=80°C



calculated based on thermal limit

Test Circuits and Waveforms

Test Circuits and Waveforms

Figure 18. Switching Time Test Circuit

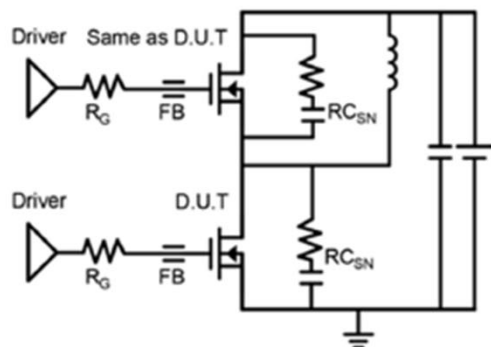


Figure 19. Switching Time Waveform

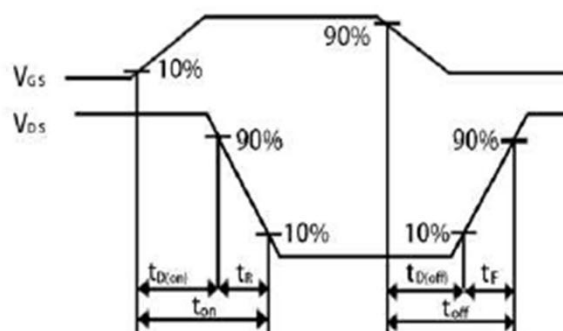


Figure 20. Dynamic $R_{DS(on)}$ Test Circuit

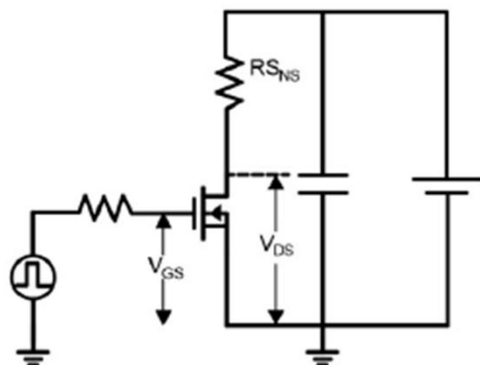


Figure 21. Dynamic $R_{DS(on)}$ Waveform

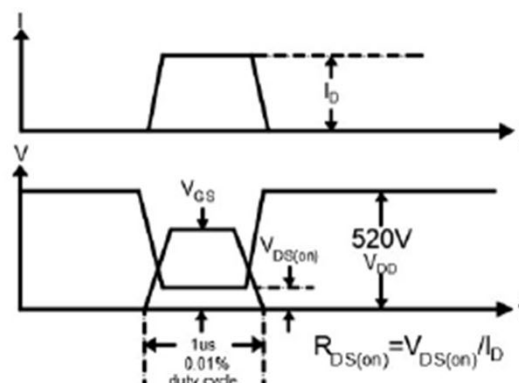


Figure 22. Diode Characteristic Test Circuits

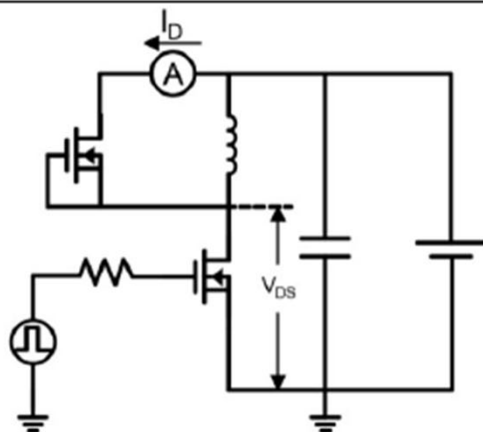
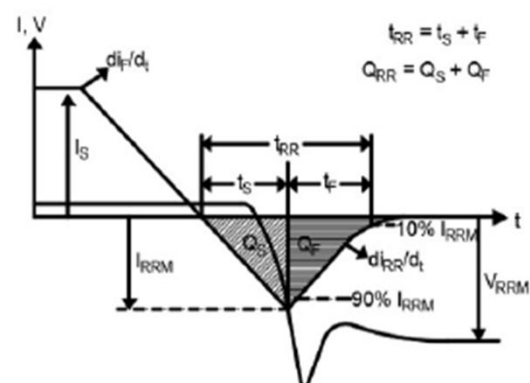
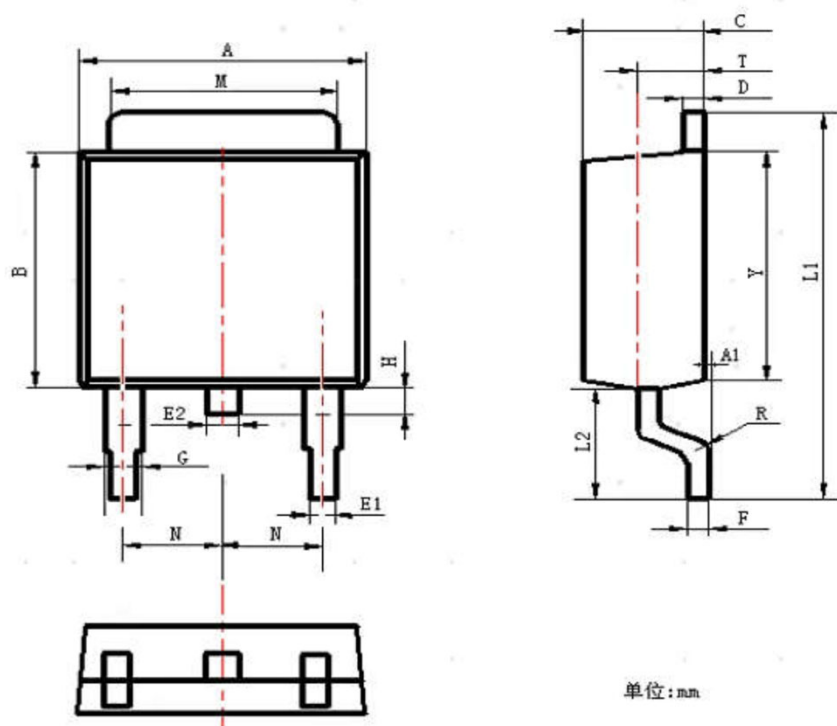


Figure 23. Diode Recovery Waveform




Product Dimension (TO-252)



SYMBOL	Millimeter		
	Min	Nom	Max
A	6.30	6.60	6.90
A1	0	0.80	0.16
B	5.70	6.00	6.30
C	2.10	2.30	2.50
D	0.30	0.60	0.90
E1	0.60	0.75	0.90
F	0.30	0.45	0.60
G	0.70	0.95	1.20
L1	9.30	9.90	10.50
L2	2.50	2.80	3.10
H	0.40	0.70	1.05
M	4.90	5.30	5.60
N	2.09	2.29	2.49


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